

Product Overview

NSBA123JDXV6: Dual PNP Bipolar Digital Transistor (BRT)

For complete documentation, see the data sheet.

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are PbFree, Halogen Free/BFR Free and are RoHS Compliant

Part Electrical Specifications

Product	Compliance	Status	Polarity	I_C Continuous (A)	V_{BRICE0} Min (V)	h_{FE} Min	R1 (k Ω)	R2 (k Ω)	R1/R2 Typ	$V_{i(off)}$ Max (V)	$V_{i(on)}$ Min (V)	Package Type
NSBA123JDXV6T5G	Pb-free Halide free	Active	Dual PNP	0.1	50	80	2.2	47	0.047	0.5	1.1	SOT-563

For more information please contact your local sales support at www.onsemi.com.

Created on: 5/25/2019